

August 2006 - Rev 02-Aug-06

CMM-9 2.0 to 9.0 GHz GaAs MMIC Amplifier

- ☐ Wide Bandwidth
- ☐ 13 dB Typical Gain
- ☐ Small Size: 39 x 35 mils
- ☐ Directly Cascadable
- ☐ Self-Biased
- ☐ Single Power Supply

Celeritek CMM-9 GaAs MMIC Amplifier

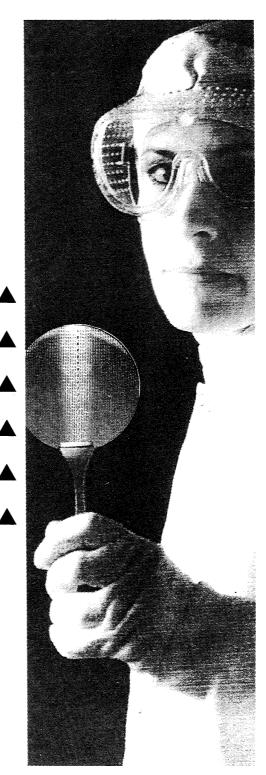
The CMM-9 is a 2 to 9 GHz GaAs MMIC amplifier. It is a two-stage feedback design which provides high gain and good power from a single power supply. Applications include oscillator buffers, RF and IF gain blocks and driver amplifiers.

The CMM-9 is a very small chip which provides 13 dB of gain and 17 dBm of power from a 6 volt supply. The chip is directly cascadable with no additional components,. The circuit's self-biasing feature provides excellent performance from a 5 to 7 volt supply. Care must be taken to isolate the input from external DC voltages.

Celeritek MMIC's are fabricated on ion-implanted GaAs material with gold-based metalization. The FET gates are sub-half micron, tee cross-section construction. Air bridges are used for top level interconnection. Silicon nitride serves as capacitor dielectric and surface passivation. Mesa resistors are used for feedback and bias functions.

The CMM-9 is available in chip form. It can be screened to meet commercial, military Hi-Rel or space grade reliability requirements. Custom wafer qualification for special electrical and/or reliability requirements is also available.







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Specifications (T _A = 25°C, V _{DD} = 6V, 2-9 GHz)								
Parameters	Units	Min	Тур	Max				
Small Signal Gain	dB	11.5	13.0					
Gain Flatness	±dB		1.5	2.0				
Input VSWR	_		1.8:1	2.0:1				
Output VSWR			1.8:1	2.0:1				
Reverse Isolation	dB	25	30					
Gain Variation Over Temperature (-55 to +95°C)	±dB		1.2	1.5				
Noise Figure	dB		5.5	6.5				
1 dB Gain Compression Power Output	dBm	15	17					
Current	mA		80	120				

Absolute Maximum Ratings

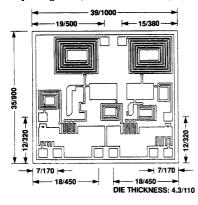
Absolute Maximum Rutings									
Rating									
8V									
1.25 W									
+175°C									
-65°C to +175°C									
+320°C									
+20 dBm									
80°C/W									

Die Attach and Bonding Procedures

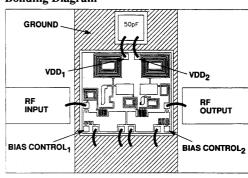
Die Attach: Conductive epoxy or preform die attach is recommended. For preform die attach: Preform: AuSn (80% Au, 20% Sn); Stage Temperature: 290°C, ±5°C; Handling Tool: Tweezers; Time: 1 min or less.

Wire Bonding: Wire Size: 0.7 to 1.0 mil in diameter (prestressed); Thermocompression bonding is preferred over thermosonic bonding. For thermocompression bonding: Stage Temperature: 250°C; Bond Tip Temperature: 150°C; Bonding Tip Pressure: 18 to 40 gms depending on size of wire.

$\boldsymbol{Chip\ Diagram\ (\text{Dimensions in mils/}\mu\text{m})}$



Bonding Diagram



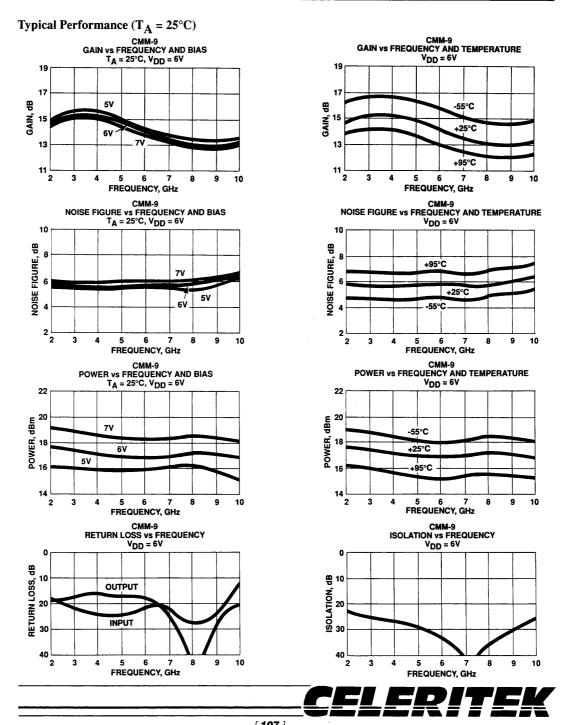


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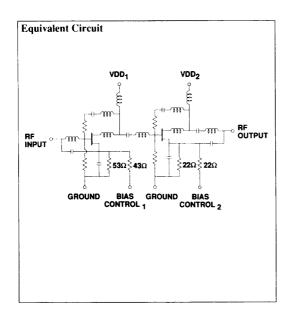
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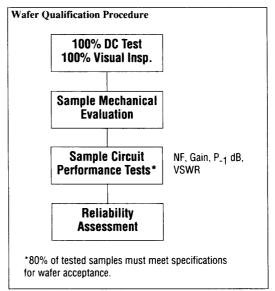
CMM-9

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Typical Scattering Parameters, $T_A = 25^{\circ}C$ (S-Parameters Include Bonding Wire Parasitics)

CMM-9										V _{DD} = 6 V			
Frequency	S ₁₁			S ₂₁		S ₁₂			S ₂₂				
(GHz)	(dB)	(Mag)	(Ang)	(dB)	(Mag)	(Ang)	(dB)	(Mag)	(Ang)	(dB)	(Mag)	(Ang)	
2.0	-18.8	0.115	-113.94	14.8	5.505	-19.71	-33.8	0.020	38.50	-19.5	0.106	-87.88	
3.0	-22.0	0.079	-126.77	15.3	5.821	-71.15	-35.3	0.017	15.38	-18.0	0.126	-133.66	
4.0	-24.7	0.058	-135.91	15.2	5.754	-118.33	-36.9	0.014	6.02	-17.0	0.141	-174.54	
5.0	-26.2	0.049	-156.87	14.8	5.495	-161.63	-39.8	0.010	1.40	-17.7	0.130	148.74	
6.0	-21.2	0.087	166.67	14.1	5.070	158.96	-43.7	0.006	10.60	-18.6	0.117	139.19	
7.0	-22.7	0.073	151.20	13.4	4.677	122.26	-51.3	0.005	27.55	-24.7	0.058	116.68	
8.0	-27.3	0.043	116.76	13.0	4.467	87.16	-46.6	0.005	107.50	-44.4	0.006	112.43	
9.0	-24.3	0.061	6.11	13.0	4.467	51.62	-40.4	0.010	124.79	-27.9	0.040	-93.09	
10.0	-13.3	0.216	-32.75	13.3	4.624	12.23	-36.0	0.016	128.34	-20.4	0.095	-84.82	





3236 Scott Boulevard Santa Clara, California 95054 (408) 986-5060 Fax: (408) 986-5095

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Specifications subject to change.



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